IN THE SPECIFICATION:

Page 3, please amend the paragraph beginning at line 24 as follows:

A liquid crystal display device of the type employing the above-discussed technology is arranged to comprise a plurality of gate lines (gate lead wires) and multiple drain lines (drain leads) formed on or over a substrate, and also to comprise switching elements'(typically, thin-f-ilmfilm transistors, as the rest of the description as will be presented below assumes the use of such thin-film transistors) at cross-over points or "intersections" of the gate and drain lines, wherein more than one common electrode and pixel electrodes driven by the switching elements are disposed adjacent to each other.

Page 4, please amend the paragraph beginning at line 19 as follows:

Fig. 17 is a diagram showing an enlarged plan view of a main part of a thin-film transistor in one exemplary IPS scheme liquid crystal display device. In Fig. 17, "GL" is used to designate a gate line; DL indicates a drain line; ASI denotes a semiconductor layer (amorphous silicon gr "a-Si" layer, also called a-Si island in some cases); PX denotes a pixel electrode; and CT denotes a common electrode. The element SC1-SD1 is a source electrode, whereas the element SD2 is a drain electrode. In this liquid crystal display device, the pixel electrode PX and common electrode CT are disposed over a thin-film transistor substrate in such a manner that these elements are in close proximity in position relative to each other. The source electrode SDISD1 and pixel electrode PX of the thin-film transistor are connected together via a through-hole TH.

Page 5, please amend the paragraph beginning at line 7 as follows:

In addition, Fig. 18 is a main part plan view diagram pictorially depicting a thin-film transistor portion in another example of the IPS li quid liquid crystal display

device. In Fig. 18 the same reference characters as those used in Fig. 17 designate the same functional parts or components. In this liquid crystal display device, the pixel electrode PX is formed directly on the thin-film transistor substrate, whereas the common electrode CT is formed to overlie the pixel electrode PX with a dielectric layer interposed therebetween. The source electrode SC1_SD1_is formed at the same layer level as the pixel electrode PX. The source electrode SC1_SD1_of the thin-film transistor is connected to the pixel electrode PX via a through-hole TH.

Page 6, please amend the paragraph beginning at line 2 as follows:

With any one of the liquid crystal display devices shown in Figs. 17 and 18 also, the semiconductor layer ASI to be formed over the gate line GL is oversized and extruded from the gate line GL at portions underlying the source electrode SC1 SD1 (i.e. the portions surrounded by circles "A" in Figs. 17-18). When back-light rays reach and fall on such extruded-portions of this semiconductor layer ASI, what is called the photoconduction current - also known as photoconductivity current in some cases - might be generated, resulting in creation of current leakage at the thin-film transistor, or alternatively a potential decrease occurs in signal hold/retention voltage. Generally this "photocon" current is derived due to, for example, an increase in conductivity of the semiconductor and/or the so-called intrinsic photoconductivity of the semiconductor which can take place due to the fact that rays of light incident on the semiconductor go beyond the forbidden band (band gap) of the semiconductor causing charge carriers to be produced inside thereof.

Page 14, please amend the paragraphs beginning at lines 16 and 26 as follows:

Several preferred embodiments of the present invention will now be described in detail with reference to the accompanying drawings. Note that although certain

embodiments with the principles of the invention being applied to IPS type liquid crystal display devices will be set <u>f-orth-forth</u> herein, the same goes with liquid crystal display devices of the TN type. Also note that parts or components with the same functionalities are identified by the same reference characters and that any repetitive explanation will be omitted.

Referring to Fig. 1, there is schematically shown a plan view of the configuration of a main part of a li-qui-d-liquid crystal display device in accordance with a first embodiment of the present invention, which part includes a thin-film transistor (TFT) section. As shown in Fig. 1, gate lines (gate lead wires, also known as scan signal lines or horizontal signal lines) GL, drain lines (drain lead wires, also called video signal lines or vertical signal lines) DL, and common lines (common leads, also called counter electrode lead wires) CL are provided on a substrate, and a respective one of the thin film transistor sections are disposed at or within cross-over (or "intersection") region of two neighboring drain lines DL and two gate lines GL.

Page 36, please amend the paragraph beginning at line 12 as follows:

The external connection terminals DTM are <u>formed formed</u> of a transparent conductive layer ITO1 and are connected to drain lines DL at a part from which the protective film PSV1 has been removed. This transparent conductive film ITO1 uses a transparent conductive film ITO which is similar to that of gate-side external connection terminals GTM. Wiring leads spanning from a display region (matrix section) up to the external connection terminals DTM are configured such that a layer d1 is constituted which is at the same level as the drain lines DL.

Page 39, please amend the paragraph beginning at line 1 as follows:

Fig. 15 is a drive signal waveform waveform diagram of the liquid crystal display device shown in Fig. 14. A gate signal VG takes an ON level once per scanning period and an OFF level during the other periods. A drain signal voltage VD is applied in such a way that it is two times greater in amplitude than a voltage to be applied to the liquid crystal layer and then transferred to a single pixel while letting the positive polarity and negative polarity be inverted in units of frames.